### NextPower 100 V, 18 m $\Omega$ N-channel MOSFET in TO220 package

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche rug	gedness						
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\begin{array}{l} {\sf I}_{\sf D} = 20.5 \; {\sf A}; \; {\sf V}_{sup} \leq \; 100 \; {\sf V}; \; {\sf R}_{\sf GS} = 50 \; \Omega; \\ {\sf V}_{\sf GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; ^{\circ}{\rm C}; \; \underline{{\sf Fig. 4}}; \\ {\sf Unclamped} \end{array}$	[2]	-	-	109	mJ

[1] Avalanche current is limited by  $I_{AS}$ 

[2] Protected by 100% test

# 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UHA
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering infor	mation		
Type number	Package		
	Name	Description	Version
PSMN018-100PSF	TO-220AB	plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body	SOT78

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN018-100PSF	PSMN018-100PSF

PSMN018-100PSF

#### NextPower 100 V, 18 m N-channel MOSFET in TO220 package

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

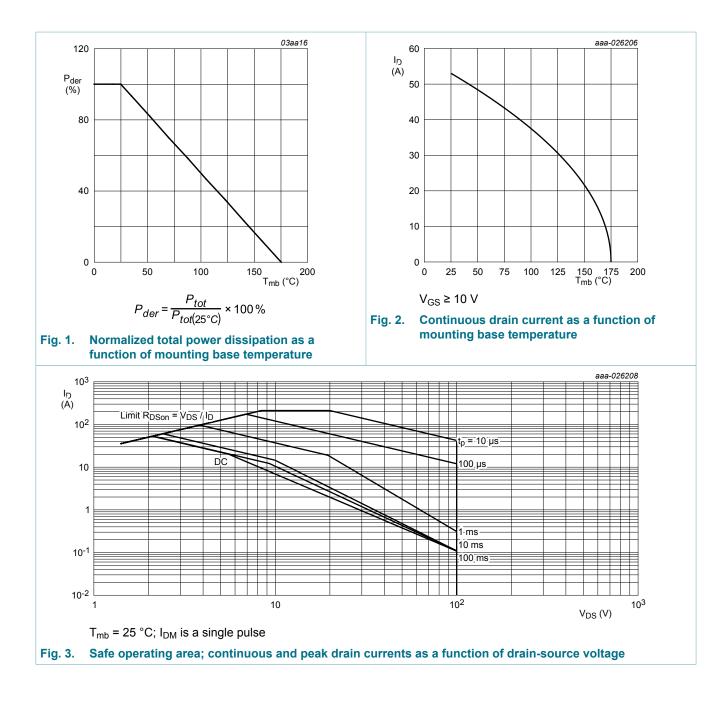
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤  T <sub>j</sub> ≤  175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤  T <sub>j</sub> ≤  175 °C; R <sub>GS</sub> = 20 kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	111	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	53	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	37	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	212	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	n diode			1		
ls	source current	T <sub>mb</sub> = 25 °C		-	53	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	212	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_{D} = 20.5 \; \text{A}; \; V_{sup} \leq \; 100 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \overline{\text{Fig. 4}}; \\ \text{Unclamped} \end{array} $	[2]	-	109	mJ
I <sub>AS</sub>	non-repetitive avalanche current		[2]	-	20.5	А

[1] Avalanche current is limited by I<sub>AS</sub>

[2] Protected by 100% test

PSMN018-100PSF

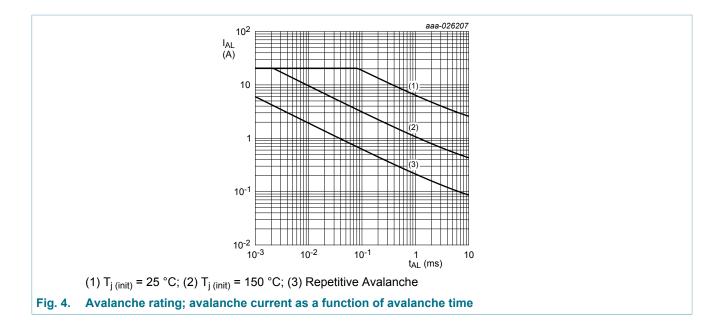
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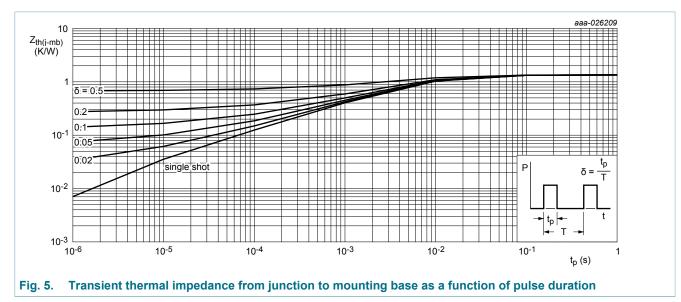
### NextPower 100 V, 18 m $\Omega$ N-channel MOSFET in TO220 package



### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	1.22	1.35	K/W



### NextPower 100 V, 18 m $\Omega$ N-channel MOSFET in TO220 package

### **10. Characteristics**

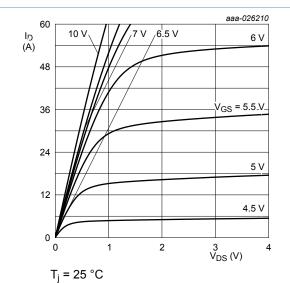
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	100	-	-	V
( )	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>i</sub> = -55 °C	-	3.6	-	V
	voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C	-	2.1	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	2	3.2	4	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-7.1	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.01	1	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	100	μΑ μΑ ηΑ ηΑ ΜΩ ΜΩ ΜΩ ΜΩ Ω
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	5	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	5	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; Fig. 10	-	14.9	18	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	17.8	27	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; Fig. 11	-	22	28 40	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; <u>Fig. 11</u>	-	31	40	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.58	-	Ω
Dynamic cha	aracteristics	· · · ·				
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 15 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	21.4	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	10.9	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	7.2	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	4.3	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	2.9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	4.2	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 50 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.9	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1482	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	280	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	13	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; $R_{L}$ = 3.3 $\Omega$ ; $V_{GS}$ = 10 V;	-	10.2	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	14.1	-	ns

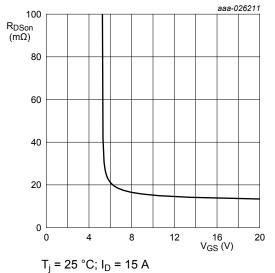
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t <sub>d(off)</sub>	turn-off delay time			-	17.3	-	ns
t <sub>f</sub>	fall time			-	12.6	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>		-	0.9	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 15 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 50 \text{ V}; \frac{\text{Fig. 16}}{100}$		-	40	-	ns
Qr	recovered charge			-	46	-	nC







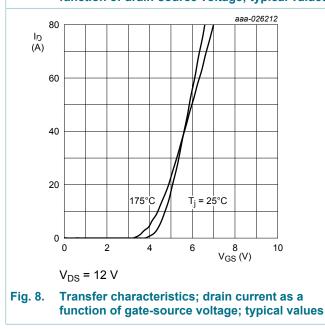
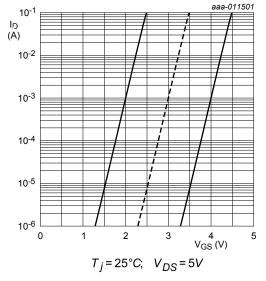


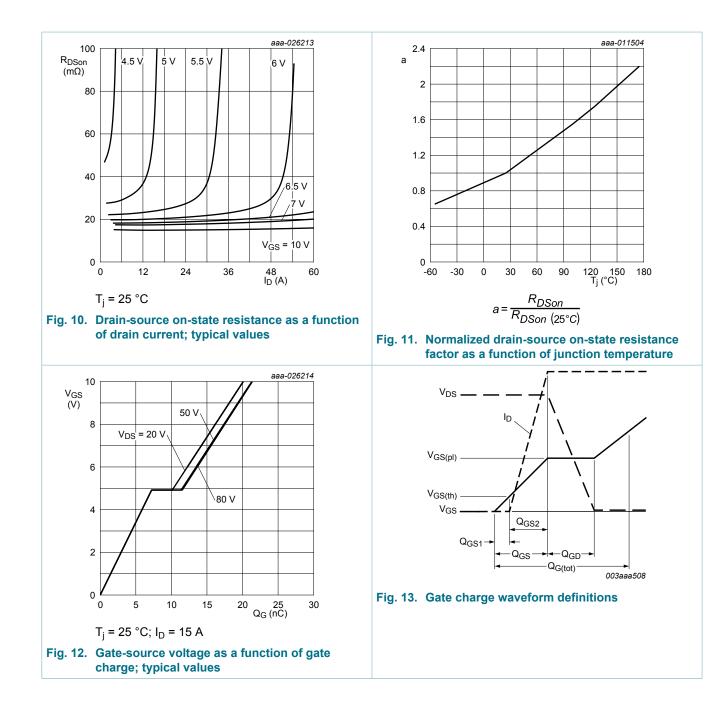
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values





**Product data sheet** 

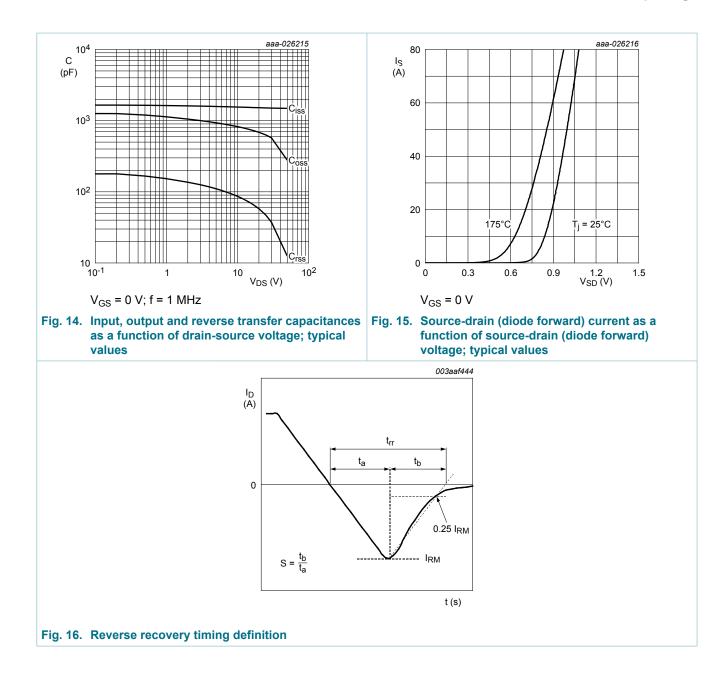
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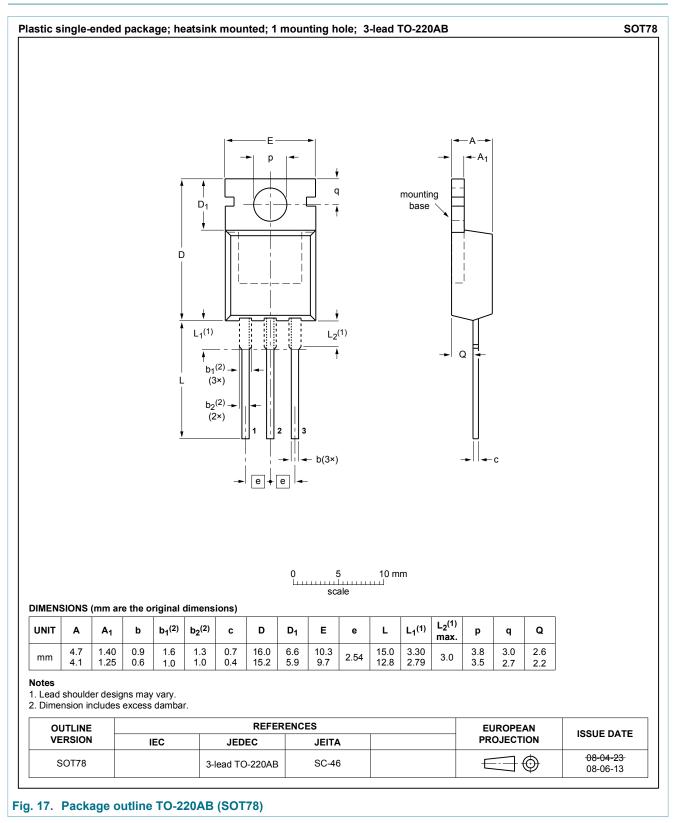
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#### NextPower 100 V, 18 m N-channel MOSFET in TO220 package



#### NextPower 100 V, 18 m N-channel MOSFET in TO220 package

### 11. Package outline



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**Product data sheet** 

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### 12. Legal information

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Document status [1][2]	Product status [3]	Definition
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### 13. Contents

1.	General description	.1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	.1
5.	Pinning information	.2
6.	Ordering information	.2
7.	Marking	. 2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	Characteristics	.6
11.	Package outline	10
12.	Legal information1	11

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